

650V N-Channel Super Junction MOSFET

Voltage	650 V	Rdson	75mΩ
Current	29.2 A	Qg	78.5nC

Feature:

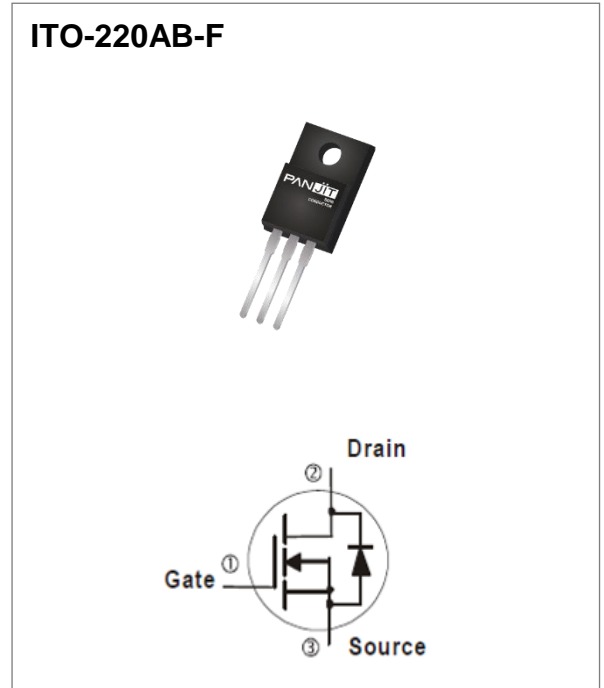
- $R_{DS(ON) Max, V_{GS}@10V}$: 75mΩ
- Body diode with fast recovery characteristics
- High Speed Switching and Low $R_{DS(ON)}$
- 100% Avalanche Tested
- 100% Rg Tested
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: ITO-220AB-F package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 2 grams

Application

- PFC/LLC/ PSFB of Industrial PSU / Battery charger.



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage @ T_{jmax}		V_{DS}	700	V
Drain-Source Voltage		V_{DS}	650	
Gate-Source Voltage		V_{GS}	± 30	
Continuous Drain Current	$T_C=25^\circ\text{C}$	I_D	29.2	A
	$T_C=100^\circ\text{C}$		18.4	
Pulsed Drain Current	$T_C=25^\circ\text{C}$	I_{DM}	102	A
Single Pulse Avalanche Energy (Note 6)		E_{AS}	180	mJ
MOSFET dv/dt ruggedness		dv/dt	120	V/ns
Diode dv/dt		dv/dt	70	V/ns
Insulation Withstand Voltage for ITO-220AB-F (Note 7)		V_{iso}	3.5	kV
Power Dissipation	$T_C=25^\circ\text{C}$	P_D	156	W
	$T_C=100^\circ\text{C}$		63	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	$^\circ\text{C}$

Thermal Characteristics

PARAMETER	SYMBOL	VALUES			UNITS	
		MIN.	TYP.	MAX.		
Thermal Resistance	Junction-to-Case (Bottom)	$R_{\theta JC}$	-	0.5	0.8	$^\circ\text{C/W}$
	Junction-to-Ambient (Note 4)	$R_{\theta JA}$	-	44.8	60	$^\circ\text{C/W}$

Electrical Characteristics (T_A = 25 °C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	650	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	3.3	4.0	4.7	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =17A (Note 1)	-	62.3	75	mΩ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =650V, V _{GS} =0V	-	-	10	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V	-	-	±100	nA
Transfer characteristics	g _{fs}	V _{DS} =20V, I _D =34A	-	36.6	-	S
Dynamic (Note 5)						
Total Gate Charge	Q _g	V _{DS} =400V, I _D =34A, V _{GS} =10V	-	78.5	-	nC
Gate-Source Charge	Q _{gs}		-	22.8	-	
Gate-Drain Charge	Q _{gd}		-	33.6	-	
Input Capacitance	C _{iss}	V _{DS} =400V, V _{GS} =0V, f=250kHz	-	3507	-	pF
Output Capacitance	C _{oss}		-	49.7	-	
Reverse Transfer Capacitance	C _{rss}		-	6.1	-	
Effective Output Capacitance Energy Related	Co(er)	V _{DS} =0V to 400V, V _{GS} =0V, f=250kHz (Note 4)	-	95	-	
Turn-On Delay Time	td(on)	V _{DD} =400V, I _D =34A, V _{GS} =10V, R _G =10Ω (Note 2)	-	44.4	-	ns
Turn-On Rise Time	t _r		-	140.6	-	
Turn-Off Delay Time	td(off)		-	71.3	-	
Turn-Off Fall Time	t _f		-	59.2	-	
Gate Resistance	R _g	f=1.0MHz	-	5.9	-	Ω
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I _S		-	-	29.2	A
Diode Forward Voltage	V _{SD}	I _S =17A, V _{GS} =0V	-	0.90	1.5	V
Reverse Recovery Charge	Q _{rr}	I _S =34A di/dt=100A/μs	-	0.97	-	uC
Reverse Recovery Time	T _{rr}		-	144.4	-	ns
Reverse Recovery Current	I _{rrm}		-	12.3	-	A

NOTES :

1. Pulse width ≤ 380us, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature typical characteristics.
3. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance.
4. C_{o(er)} is a capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0V to 400V.
5. Guaranteed by design, not subject to production testing.
6. E_{AS} is calculated based on the condition of L = 10 mH, I_{AS} = 6 A, V_{DD} = 50 V, V_{GS} = 10 V and 100% test by L=0.1mH. I_{as}= 7.5A in mass production.
7. It's 100% test during mass production by V_{dc}= 3.5kV with 1sec.

TYPICAL CHARACTERISTIC CURVES

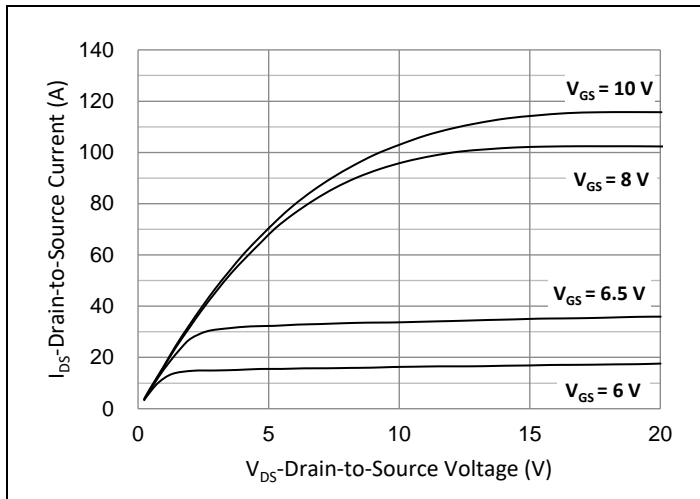


Fig.1 Output Characteristics

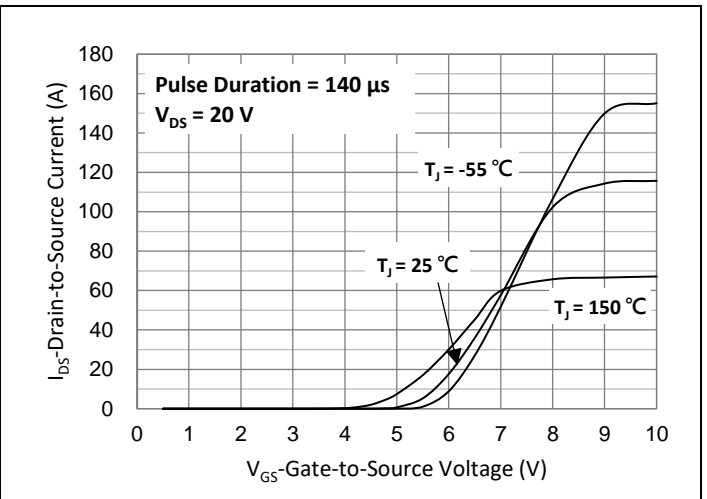


Fig.2 Transfer Characteristics

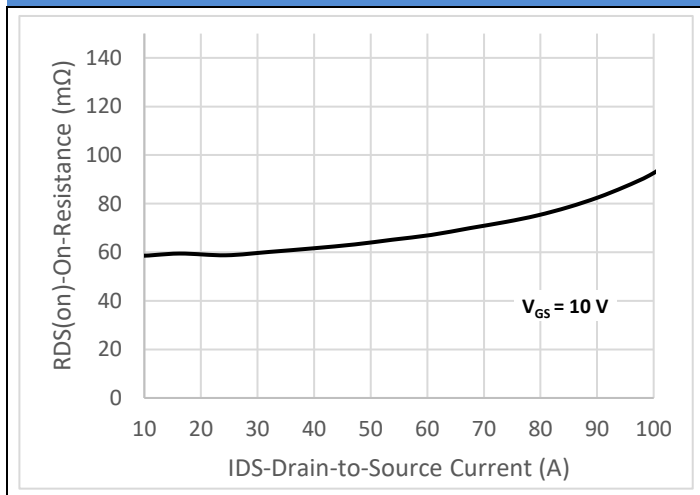


Fig.3 On-Resistance vs. Drain Current

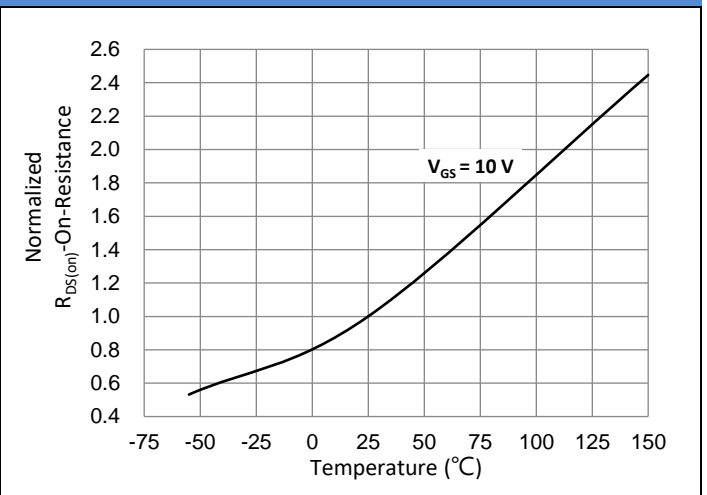


Fig.4 On-Resistance vs. Junction Temperature

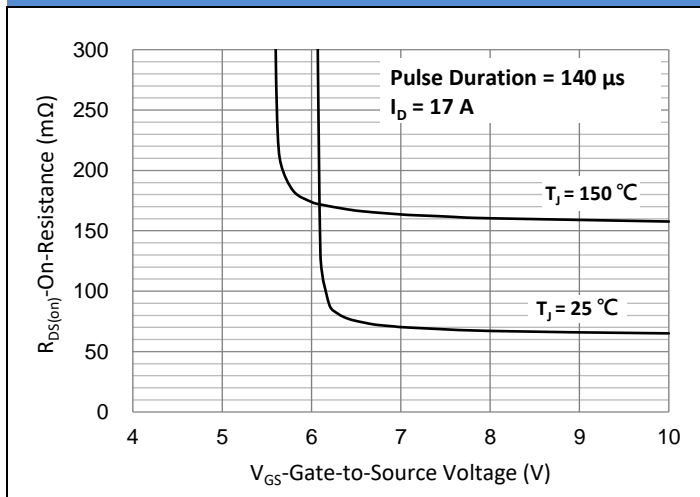


Fig.5 Capacitance vs. Drain-Source Voltage

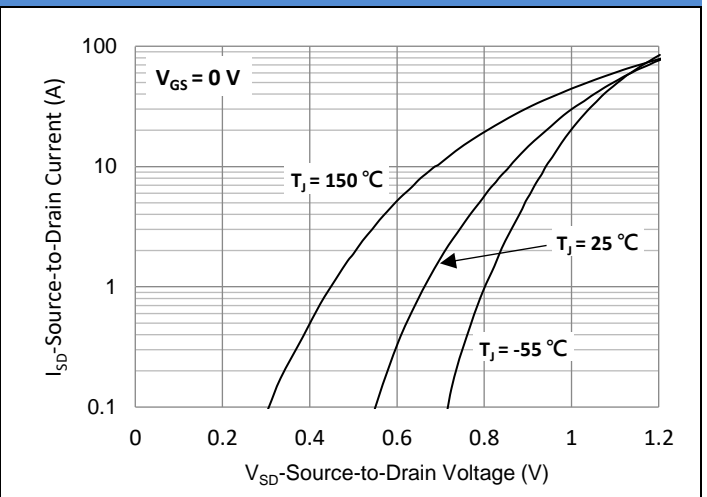


Fig.6 Source-Drain Diode Forward Voltage

TYPICAL CHARACTERISTIC CURVES

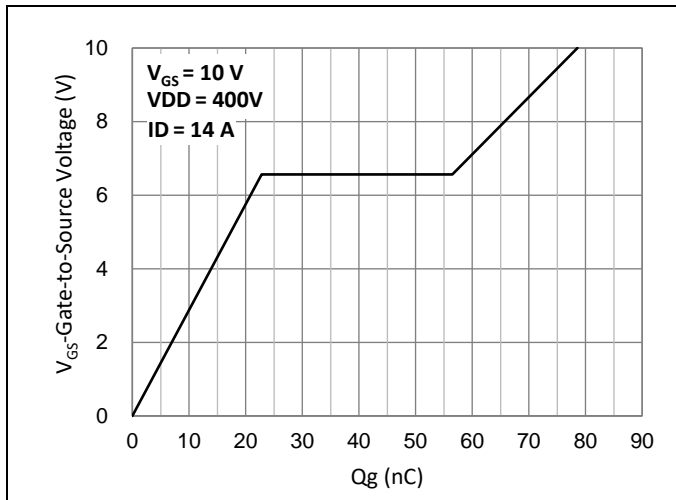


Fig.7 Gate-Charge Characteristics

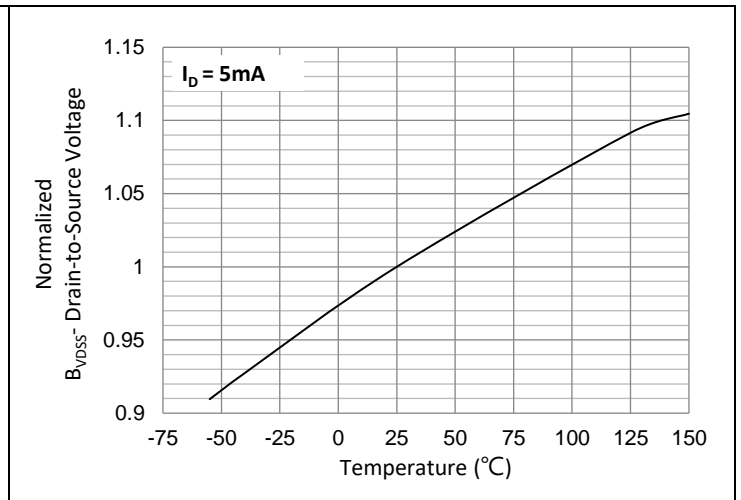


Fig.8 Breakdown Voltage Variation vs. Temperature

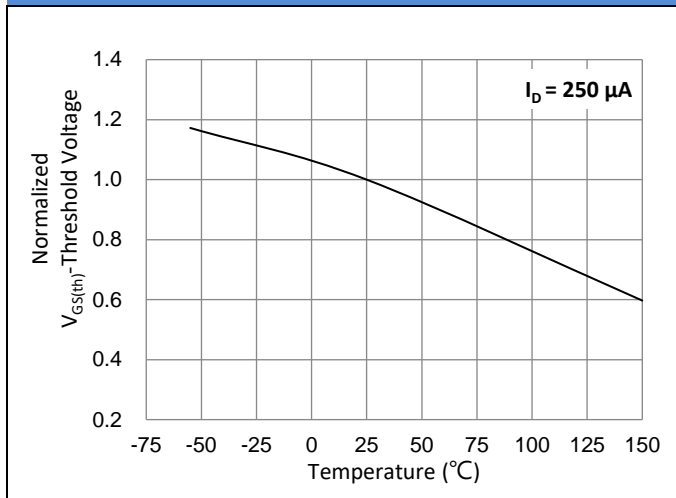


Fig.9 Threshold Voltage Variation with Temperature

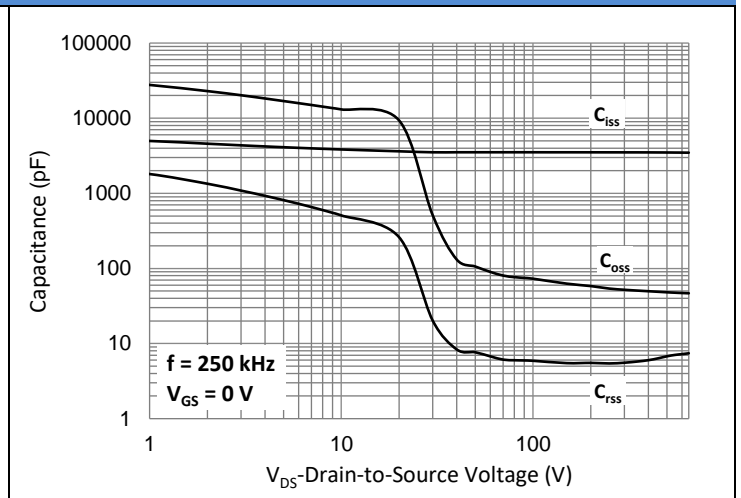


Fig.10 Drain Current vs. Case Temperature

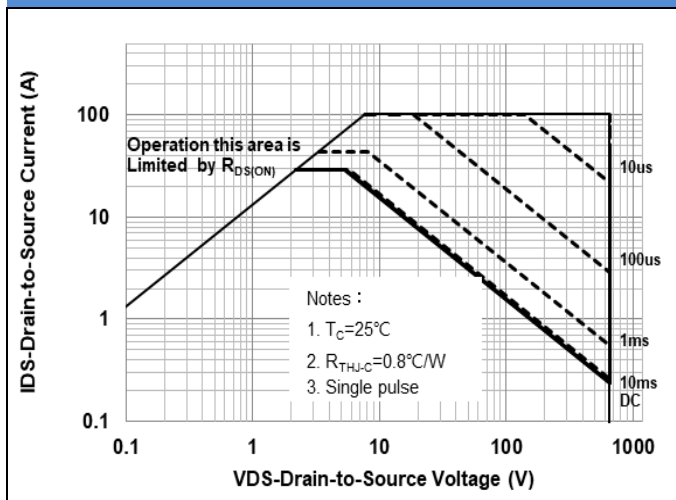


Fig.11 Maximum Safe Operating Area

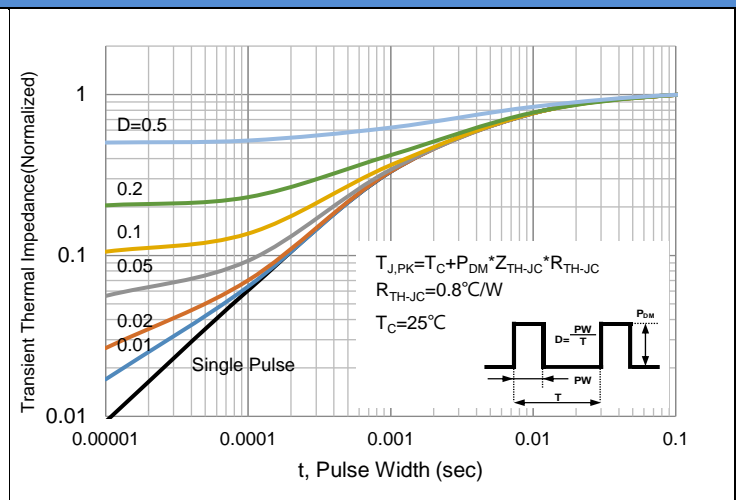


Fig.12 Normalized Transient Thermal Impedance

TYPICAL CHARACTERISTIC CURVES

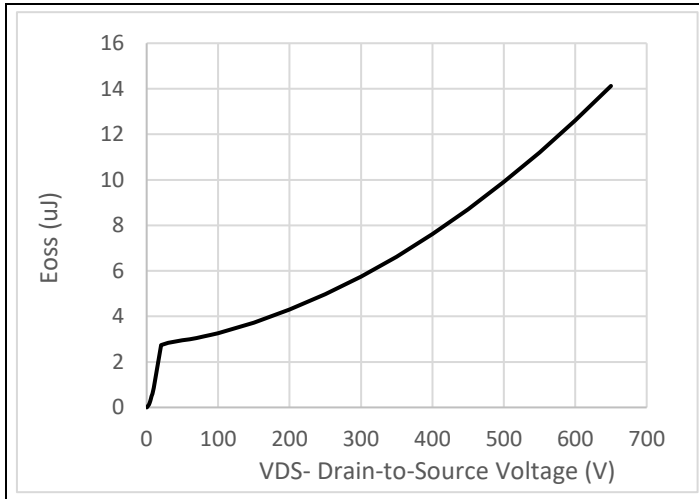
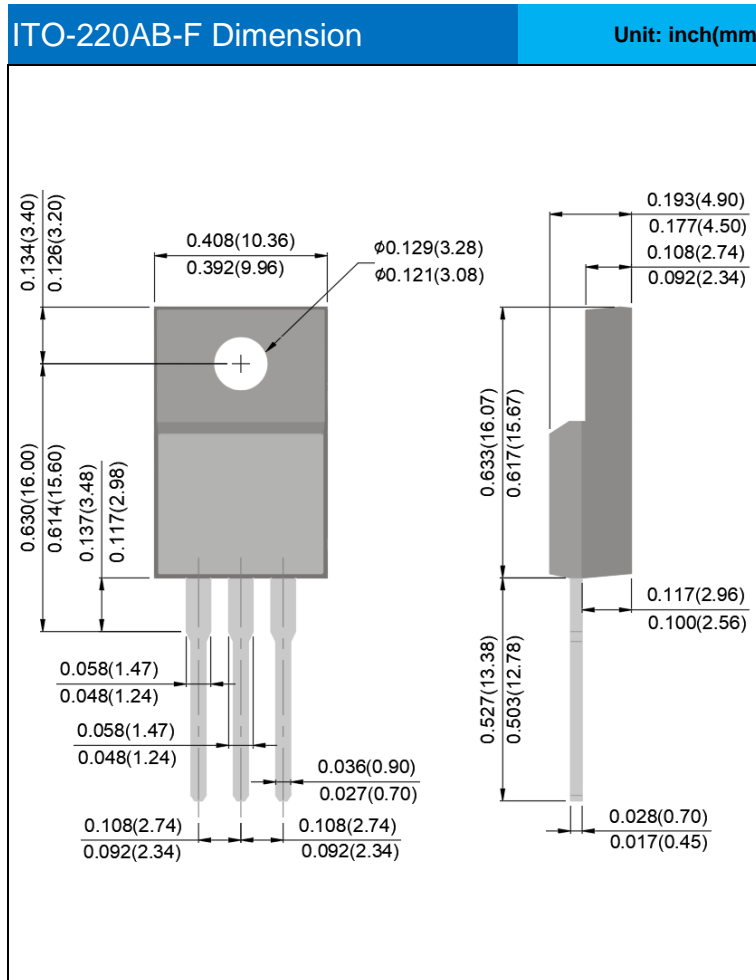


Fig.13 Typ. Coss Stored Energy

Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJMF080N65FR2	ITO-220AB-F	50pcs / Tube	080N65FR2

Packaging Information



Marking Diagram

PJ	Y = Year Code
080N65FR2	W = Week Code (A~Z)
YWLL x	LL = Lot Code (00~99)
	x = Production Line Code

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